L Number	Hits	Search Text	DB	Time stamp
21	1	6335292.pn.	USPAT	2004/02/05 14:23
22	313	Li-Li.in.	USPAT;	2004/02/05
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	14:23
23	41	Howard-Bradley-J.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:24
24	105	Li-Li.in. and @ay<=1999	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05
25	189	(plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/02/05
26	613	(CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:27
28	523	((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma ) and @ay<=2001	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:27
29	357	(((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma ) and @ay<=2001) and power	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:28
30	328	((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma ) and @ay<=2001) and power) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:28
31	284	(((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma ) and @ay<=2001) and power) and semiconductor) and ((etch or etching)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 14:29
32	222	same (SiO or siO?sub.2 or oxide)) (((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor) and ((etch or etching) same (SiO or siO?sub.2 or oxide) same plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:29
_	1	6159794.pn.	USPAT	2003/01/08 09:16
_	17451	plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))	USPAT	2003/04/16
_	160	(plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)	USPAT	2004/02/05 14:24
_	124	((plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)) and (chlorine or Cl?sub.2 or HBr or bromic or CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or inert or argon or Ar or helium or he)	USPAT	2003/04/16 13:13

[	102	(((plasma and semiconductor and (etching	USPAT	2003/01/08
_	102	same (oxide or SiO or SiO?sub.2))) and	OSPAI	13:09
		(second adj power)) and (chlorine or		
		Cl?sub.2 or HBr or bromic or CF?sub.4 or		
		CHF?sub.3 or "CH.sub.2 F.sub.2" or inert		
	1	or argon or Ar or helium or he)) and		
		(argon or Ar or helium or he)		
_	2786	CF?sub.4 with CHF?sub.3	USPAT	2003/04/16
	2247	(GROUND A soith GYROUND 2) and allege	HCDAM	13:11
_	2247	(CF?sub.4 with CHF?sub.3) and plasma	USPAT	2003/04/16
_	452	CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2003/01/08
	152	argon or argon or helium or he)		14:14
_	372	(CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2004/02/05
		argon or argon or helium or he)) and		14:26
		plasma		
_	260	((CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2003/01/08
		argon or argon or helium or he)) and		13:10
	222	plasma) and power	HGDAM	2002/01/00
	223	(((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and	USPAT	2003/01/08
		plasma) and power) and ((etch or etching)		14.20
		same (oxide or SiO or SiO?sub.2))		
_	188	((((CF?sub.4 with CHF?sub.3 with (inert	USPAT	2003/01/08
		or argon or argon or helium or he)) and		13:12
		plasma) and power) and ((etch or etching)		
		same (oxide or SiO or SiO?sub.2))) and		
	100	(watt or W)		0000/01/00
-	183	, , , , ,	USPAT	2003/01/08
		or argon or argon or helium or he)) and plasma) and power) and ((etch or etching)		13:12
ļ		same (oxide or SiO or SiO?sub.2))) and		
		(watt or W)) not (((plasma and		
		semiconductor and (etching same (oxide or		
		SiO or SiO?sub.2))) and (second adj		
		power)) and (chlorine or Cl?sub.2 or HBr		
		or bromic or CF?sub.4 or CHF?sub.3 or		
		"CH.sub.2 F.sub.2" or inert or argon or		
	201	Ar or helium or he)) CF?sub.4 with CHF?sub.3 with (helium or	USPAT	2003/01/08
	201	he)	USPAI	14:15
_	2	((CF?sub.4 with CHF?sub.3 with (helium or	USPAT	2003/01/08
	_	he)) and plasma) and ((germanium or Ge)	332772	14:15
		with substrate)		
-	162		USPAT	2003/01/08
		he)) and plasma		14:22
-	9465	(germanium with substrate) or (gallium	USPAT	2003/01/08
	2021	with arsenide with substrate)   ((germanium or Ge) with substrate) and	IICDAM	14:23 2003/01/08
	2021	((gallium or Ga) with (arsenide or As or	USPAT	14:26
		GaAs) with substrate)		11.20
_	883	(((germanium or Ge) with substrate) and	USPAT	2003/01/08
		((gallium or Ga) with (arsenide or As or		14:26
		GaAs) with substrate)) and plasma		
_	1	6159794.pn. and ((etch or etching) same	USPAT	2003/01/08
	370	(oxide or SiO or SiO?sub.2))	, , , , , , , , , , , , , , , , , , ,	14:27
-	378	((((germanium or Ge) with substrate) and	USPAT	2003/01/08
		((gallium or Ga) with (arsenide or As or GaAs) with substrate)) and plasma) and		14:27
		((etch or etching) same (oxide or SiO or		
		(SiO?sub.2))		
_	210	((((germanium or Ge) with substrate) and	USPAT	2003/01/08
1		((gallium or Ga) with (arsenide or As or		16:19
		GaAs) with substrate)) and plasma) and		
		((etch or etching) same (oxide or SiO or		
	40035	SiO?sub.2))) and power	110000	2002/04/16
-	40037	(etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)	USPAT	2003/04/16 13:08
_	19320	((etch or etching) with (oxide or dioxide	USPAT	2003/04/16
	15520	or SiO or SiO?sub.2)) and plasma	OSIAI	13:06
L	L		1	

_	4689	(((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or	USPAT	2003/04/16 13:09
		etching))		
-	21441	(etch or etching) with ((silicon adjoxide) or (silicon adj dioxide) or SiO or	USPAT	2003/04/16
		SiO?sub.2)		13:08
_	3205	((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma)	USPAT	2003/04/16
		and ((power or watts) same (etch or		, 10.00
		etching))) and ((etch or etching) with		
		((silicon adj oxide) or (silicon adj		
_	2225	dioxide) or SiO or SiO?sub.2)) (((((etch or etching) with (oxide or	USPAT	2003/04/16
		dioxide or SiO or SiO?sub.2)) and plasma)	USIAI	13:10
		and ((power or watts) same (etch or		
		etching))) and ((etch or etching) with		
		((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and		
		(Cl?sub.2 or Cl2 or HBr or hydro&lbromic		
		or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
		or "CH.sub.2 F.sub.2")		
-	664	((((((etch or etching) with (oxide or	USPAT	2003/04/16
		dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or		13:11
		etching))) and ((etch or etching) with		
		((silicon adj oxide) or (silicon adj		
		dioxide) or SiO or SiO?sub.2))) and		
		(Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
		or "CH.sub.2 F.sub.2")) and (CF?sub.4		
		with CHF?sub.3)		
[ -	541	((((((etch or etching) with (oxide or	USPAT	2003/04/16
		<pre>dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or</pre>		13:11
		etching))) and ((etch or etching) with		
		((silicon adj oxide) or (silicon adj		
		dioxide) or SiO or SiO?sub.2))) and		
		(Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
		or "CH.sub.2 F.sub.2")) and (CF?sub.4		
		with CHF?sub.3)) and @py<=2001		
-	492	(((((((etch or etching) with (oxide or	USPAT	2003/04/16
		dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or		13:17
		etching))) and ((etch or etching) with		
		((silicon adj oxide) or (silicon adj		
ļ		dioxide) or SiO or SiO?sub.2))) and		
		(Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
		or "CH.sub.2 F.sub.2")) and (CF?sub.4		
		with CHF?sub.3)) and @py<=2001) and		
	425	second		
-	425	<pre>(((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma)</pre>	USPAT	2003/04/16 13:14
		and ((power or watts) same (etch or		10.11
		etching))) and ((etch or etching) with		
		((silicon adj oxide) or (silicon adj		
		dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic		
		or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
		or "CH.sub.2 F.sub.2")) and (CF?sub.4		,
		with CHF?sub.3)) and @py<=2001) and		
		second) and (inert or argon or Ar or helium or he)		
L				

192   (((((((teth or etching) with (oxide or oxide or sio or sio7sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or Sio or Sio7sub.2)) and ((cl?sub.2 or Cl2 or HBr or hydroslbromic or CP4 or CP7sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CP7sub.4 with CHF?sub.3)) and (epy<-2001) and (second with power) (((((((((te(ch or etching) with (oxide or etching)))) and ((cl) or CP4 or CP7sub.4 or CHF?sub.3)) and (eps) and ((cl) or cetching)) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or Sio or Sio7sub.2)) and (CP7sub.4 with CHF?sub.3)) and (epy<-2001) and second) and (inert or argon or Ar or helium or hel) and (second with power) (((((((((te(ch or etching) with (oxide or dioxide or Sio or Sio7sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching)) and ((cl) or siorsub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((cl) or Siorsub.2)) and (cl) or CP4 or CP7sub.4 or CHF7sub.3) or CHF3 or "CH.sub.2 F.sub.2")) and (cl) or CP4 or CP7sub.4 or CHF7sub.3) or CHF3 or "CH.sub.2 F.sub.2")) and (cl) or CP4 or CP7sub.4 or CHF7sub.3) and second) and (second with power) or CP4 or CP7sub.4 or CHF7sub.3) and (power or watts) same (etch or etching)) and ((etch or etching) with (oxide or Sio or Siorsub.2)) and (cl) or CP4 or CP7sub.4 or CHF7sub.3 or CHF3 or "CH.sub.2 F.sub.2") and (CP3ub.4 with CHF7sub.3)) and (epy<-2001) and second with power) or CP4 or CP7sub.4 or CHF7sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CP3ub.4 with CHF7sub.3)) and (epy<-2001) and (second near3 power)  - 2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48 USPAT 2003/04/16 15:08 13:48 USPAT 13:48				· · · · · · · · · · · · · · · · · · ·	
etching))) and ((etch or etching) with ((silicon adj oxide) or Silorsub.2))) and (C(17sub.2 or C12 or HBr or hydro*lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CHF3 ub.2 F.sub.2")) and (CP?sub.4 with CHF?sub.3)) and @py<=2001) and (second with power)  179 (((((((((etch or etching) with (oxide or dioxide or Si0 or Si0?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with (oxide or dioxide) or Si0 or Si0?sub.2))) and plasma) and ((power or watts) same (etch or etching)) and ((clrsub.2 or C12 or HBr or hydro*lbromic or CF4 or CF?sub.4 or CHF?sub.3) or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (inert or argon or Ar or helium or he)) and (second with power)  [((((((((etch or etching) with (oxide or dioxide or Si0 or Si0?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or Si0 or Si0?sub.2)) and (Cl?sub.2 or Cl2 or HBr or hydro*lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CP?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (second with power)  [(((((((tetch or etching) with (oxide or dioxide or Si0 or Si0?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with (oxide or dioxide or Si0 or Si0?sub.2)) and plasma) and ((power or watts) same (etch or ctching)) and ((etch or etching) with (oxide or dioxide or Si0 or Si0?sub.2)) and plasma) and ((cl?sub.2 or Cl2 or HBr or hydro*lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 or CHF3 or "CH.sub.2 f.sub.2")) and (Spot CHF3 or "CH.sub.3) and Spot CHF3 or "CH.sub.2 f.sub.2") and (Spot CHF3 or "CH.sub.3) and Spot CHF3 or "CH.sub.2 f.sub.2") and (Spot CHF3 or "CH.sub.2 f.sub.2") and (Spot CHF3 or "CHF3 or "CH.sub.2 f.sub.2") and (Spot CHF3 or "CHF3 or "CH.sub.2 f.sub.2") and (Spot CHF3 or	_	192		USPAT	
Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CP4 or CP7sub.4 or CH7sub.3 or CP4 or CP3sub.4 or CH7sub.4 with CH7sub.3) and GPy<=2001 and (second with power) (((((((((((tch or etching) with (oxide or etching))) and ((power or watts) same (etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and plasma) and ((l?sub.2 or Cl2 or HBr or hydro&lbromic or CP4 or CF7sub.4 or CH7sub.3 or CH73 or "CH.sub.2 F.sub.2")) and (CP7sub.4 with CHP?sub.3) and (second with power) ((((((((ctch or etching) with ((silicon adj oxide) or (silicon adj oxide) or helium or he)) and (second with power) ((((((((ctch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((cl?sub.2 or Cl2 or HBr or hydro&lbromic or CP4 or CF7sub.4 or CHF7sub.3) or CH3 or "CH.sub.2 F.sub.2")) and (CP7sub.4 with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (cl?sub.2 or Cl2 or HBr or hydro&lbromic or CP4 or CF7sub.4 or CHF7sub.3 or CH3 or "CH.sub.2 F.sub.2")) and (cP7sub.4 with CHP?sub.3)) or Mad (second with power) ((((((((ctch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching)) and ((cfch or etching) with (oxide or dioxide) or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and plasma) and (CP7sub.2 or Cl2 or HBr or hydro&lbromic or CP4 or CF7sub.4 or CHF3bub.3 or CFF3 or "CFF3 or "CF7 or			etching))) and ((etch or etching) with		
or "CH. sub.2 F. sub.2")) and (CF?sub.4 with CHF?sub.3) and (Bpy<=2001) and (second with power)  (((((((((((teth or etching) with (oxide or dioxide or Si0 or Si0?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or Si0 or Si0?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3) and (EF?sub.4 with CHF?sub.3)) and (gpy<=2001) and second) and (inert or argon or Ar or helium or he)) and (second with power)  ((((((((((etch or etching) with (oxide or dioxide or Si0 or Si0?sub.2))) and plasma) and ((((silicon adj oxide) or (silicon adj dioxide) or Si0 or Si0?sub.2)) and plasma) and ((((silicon adj oxide) or (silicon adj dioxide) or Si0 or Si0?sub.2)) and ((((silicon adj oxide) or (silicon adj dioxide) or CF4 or CF?sub.4 with (HF?sub.3)) and ((EF?sub.3 or CHF3) or "CH. sub.2 F. sub.2")) and ((Cf?sub.2 or CF4 or CF?sub.4 or CFF?sub.3) or CHF3) or "CH. sub.2 F. sub.2")) and plasma) and (((((((((((cth or etching) with (oxide or dioxide or Si0 or Si0?sub.2))) and plasma) and (((((((((((cth or etching) with (oxide or dioxide or Si0 or Si0?sub.2))) and plasma) and (((((((((((cth or etching) with (oxide or etching)))) and (((((((((((cth or etching) with (oxide or etching)))) and ((((((((((((cth or etching) with (oxide or etching)))) and (((((((((((cth or etching) with (oxide or etching)))) and (((((((((((cth or etching) with (oxide or (((((((((((((((((((((((((((((((((((		٤	(Cl?sub.2 or Cl2 or HBr or hydro&1bromic		
(second with power)			or "CH.sub.2 F.sub.2")) and (CF?sub.4		
and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj) dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydroslbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and (ppx<=2001) and second) and (inert or argon or Ar or helium or hel) and (second with power) ((((((((((ctch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and ((Cl?sub.2 or Cl2 or HBr or hydroslbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and (ppx<=2001) and second) and (second with power) ((((((((((cth or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (CP?sub.4 or CHF?sub.3) and (CP?sub.4 or CHF?sub.3)) and (CP?sub.4 with CHF?sub.3)) and (Ppx<=2001) and (second with CHF?sub.3) and (Ppx<=2001) and (second ear3 power)  2 5726499.pn. 5710067.pn. USPAT 2003/04/16 13:48  2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34  1 6335292.pn. USPAT 2003/04/16 15:08		179	<pre>(second with power) ((((((((((etch or etching) with (oxide or</pre>	USPAT	2003/04/16
((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and ((Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7:sub.4 or CHF7:sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF7:sub.4 with CHF?sub.3)) and @py<=2001) and second mode or SiO or SiO?sub.2)) and plasma) and ((((((((((ctch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and ((Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7:sub.4 or CHF7:sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF7:sub.4 with CHF7:sub.3)) and (py<=2001) and second) and (second with power)  (((((((((ctch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((cfc) or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and ((cfc) or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7:sub.4 or CHF7:sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF7:sub.4 with CHF7:sub.3)) and @py<=2001) and (second mear3 power)  - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 13:48 - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34 - 1 6335292.pn.			and ((power or watts) same (etch or		13:28
or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (inert or argon or Ar or helium or he)) and (second with power)  ((((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydrofalbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (second with power)  ((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and plasma) and ((power or watts) same (etch or etching))) and (etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydrofalbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48  2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34  1 6335292.pn. USPAT 2003/04/16 15:08			((silicon adj oxide) or (silicon adj		
with CHF?sub.3) and @py<=2001) and second) and (inert or argon or Ar or helium or he)) and (second with power)   192			or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
helium or he)) and (second with power)			with CHF?sub.3)) and @py<=2001) and		
and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (C1?sub.2 or C12 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (second with power) ((((((tch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (C1?sub.2 or C12 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  - 2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48  - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34  - 1 6335292.pn. USPAT 2003/04/16 15:08	_	192	(((((((etch or etching) with (oxide or	USPAT	
dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (second with power)  ((((((((tetch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj dioxide) or SiO?sub.2))) and ((cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  2 5726449.pn. 5710067.pn.  2 5726499.pn. 5710067.pn.  4 6335292.pn.  USPAT 2003/04/16 11:08			and ((power or watts) same (etch or		13:28
or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (second with power)  ((((((((tetch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (C1?sub.2 or C12 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  2 5726449.pn. 5710067.pn.  1 6335292.pn.  USPAT 2003/04/16 13:48 2003/04/16 14:34 2003/04/16 15:08			dioxide) or SiO or SiO?sub.2))) and		
with CHF?sub.3)) and @py<=2001) and second) and (second with power)  (((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and ((cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  2 5726449.pn. 5710067.pn.  2 5726499.pn. 5710067.pn.  4 6335292.pn.  USPAT 2003/04/16 11:08			or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  - 2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48 - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34 - 1 6335292.pn. USPAT 2003/04/16 15:08		60	with CHF?sub.3)) and @py<=2001) and second) and (second with power)	110.53.00	2002/04/16
((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (C1?sub.2 or C12 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  - 2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48 - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34 - 1 6335292.pn. USPAT 2003/04/16 15:08			dioxide or SiO or SiO?sub.2)) and plasma)	USPAT	
(Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)  - 2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48  - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34  1 6335292.pn. USPAT 2003/04/16 15:08			((silicon adj oxide) or (silicon adj		
<pre>with CHF?sub.3)) and @py&lt;=2001) and     (second near3 power)  5726449.pn. 5710067.pn.  USPAT</pre>			(Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
- 2 5726449.pn. 5710067.pn. USPAT 2003/04/16 13:48 - 2 5726499.pn. 5710067.pn. USPAT 2003/04/16 14:34 - 1 6335292.pn. USPAT 2003/04/16 15:08			with CHF?sub.3)) and @py<=2001) and		
- 1 6335292.pn. USPAT 2003/04/16 15:08	_	2	5726449.pn. 5710067.pn.	USPAT	
15:08	_		•		14:34
	-		•		15:08
- 1 6335292.pn. USPAT 2003/10/10	_	1	6335292.pn.	USPAT	2003/10/10
- 0 Bradley-Howard.in.	-	0	Bradley-Howard.in.		2003/10/10
- 0 Bradley-Howard-J.in. USPAT; 2003/10/10 US-PGPUB 10:05	_		_	USPAT; US-PGPUB	2003/10/10 10:05
- 208 Li-Li.in. USPAT; 2003/10/10 US-PGPUB 10:05	<del>-</del>			US-PGPUB	10:05
US-PGPUB 10:06 USPAT; 2003/10/10		124	_	US-PGPUB USPAT;	10:06 2003/10/10
- 87 Li-Li.in. and plasma	_	87	Li-Li.in. and plasma	USPAT;	2003/10/10
- 25 (Li-Li.in. and (etch or etching)) and USPAT; 2003/10/10 (Li-Li.in. and plasma) and power US-PGPUB 10:07		25		USPAT;	2003/10/10

_	179	(plasma and semiconductor and (etching	USPAT	2003/10/10
		same (oxide or SiO or SiO?sub.2))) and		12:55
		(second adj power)		
_	141	((plasma and semiconductor and (etching	USPAT	2003/10/10
		same (oxide or SiO or SiO?sub.2))) and		12:54
		(second adj power) ) and @ay<=1999		
-	1	6174451.pn.	USPAT	2003/10/10
		-		11:59
	109	(plasma and semiconductor and (etching	USPAT	2003/10/10
		same ((silicon adj oxide) or SiO or		12:55
		SiO?sub.2))) and (second adj power)		
_	71	((plasma and semiconductor and (etching	USPAT '	2003/10/10
İ		same ((silicon adj oxide) or SiO or		13:43
		SiO?sub.2))) and (second adj power) ) and		
		@ay<=1998		
-	2	5726499.pn. 5710067.pn.	USPAT	2003/10/10
				13:44